Part Number Customer						
Category	Parameter		Specification	Measurement Method		
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm			
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor		
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor		
	4.0	Secondary Flat Orientation	none			
	5.0	Overall Thickness	411.00 +/- 12.00 μm	ADE, 100%		
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process		
	7.0	Bow	<70.00µm	ADE to ASTM F534, 20%		
	8.0	Warp	<70.00µm	ADE to ASTM F657, 20%		
	9.0	Edge Chips	0	Bright Light, 100%		
	10.0	Edge Exclusion	5mm			
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor		
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor		
	13.0	Handle Thickness	350.00 +/- 10.00 μm	ADE, 100%		
	14.0	Handle Doping Type	N	Wafer Vendor		
	15.0	Handle Dopant	Phosphorous	Wafer Vendor		
	16.0	Handle Resistivity	1 ~ 10 Ohmcm	Wafer Vendor		
	17.0	Backside Finish	Polished with oxide and lasermark	Wafer Vendor		
BuriedOxide	18.0	Oxide Type	Thermal			
	19.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%		
	20.0	Oxide formed on	Handle and/or device wafer			
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor		
	22.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor		
	23.0	Nominal Thickness	60.00 +/- 1.00 μm	ADE single point, 100%		
	24.0	Distance to device silicon edge from wafer edge	3 +/- 1 mm, by edge definition	Typical by Process		
	25.0	Device Doping Type	Ν	Wafer Vendor		
	26.0	Device Dopant	Phosphorous	Wafer Vendor		
	27.0	Device Resistivity	0.001 ~ 0.005 Ohmcm	Wafer Vendor		
	28.0	Voids	0	Bright Light, 100% (note 2)		
	29.0	Scratches	0	Bright Light, 100% (note 2)		
	30.0	Haze	none	Bright Light, 100% (note 2)		

Icemos Technology Ltd

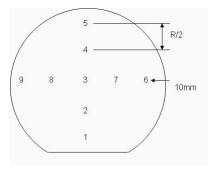
Product Specification

1000.570301

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information